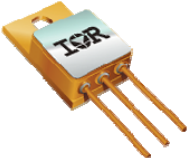



# PRODUCT CHANGE NOTICE

1. TITLE <b>IRHMS57064, Test Characteristics</b>		2. DOCUMENT NUMBER <b>FV5-C-16-004</b>	
		3. DATE <b>November 5, 2015</b>	
4. MANUFACTURER AND ADDRESS <b>International Rectifier 205 Crawford Street Leominster, MA 01453</b>		5. MANUFACTURER PART NUMBER <b>See below for IR Part Number</b>	
		6. BASE PART <b>NA</b>	
		7. NATIONAL STOCK NUMBER (NSN) <b>NA</b>	
8. CAGE <b>69210</b>	9. EFFECTIVE DATE <b>November 5, 2015</b>	10. GOVERNMENT NUMBER <b>NA</b>	
11. POINT OF CONTACT <b>Manufacturer's Representative or Customer Service Representative (978) 534-5776</b>		12. DRAWING NUMBER <b>NA</b>	
		13. SPECIFICATION NUMBER <b>MIL-PRF-19500</b>	
14. PRODUCT CHANGE This GIDEP PCN is to announce a change in the electrical characteristics for the following International Rectifier Part No listed below. This change is also coordinated with MIL-PRF-19500/698 change from revision E to F.			
<b>IRHMS57064 (JANSR2N7470T1)</b> 60V 100kRad Hi-Rel Single N-Channel TID Hardened MOSFET in a TO-254 Low-Ohmic package			
			
Electrical Characteristics @ Tj = 25°C, RDS(on) [Static Drain-to-Source On-State Resistance], with test condition of VGS = 12V, ID = 45A Change RDS(on) Max limit from 0.0066 Ω to 0.0076 Ω			
Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation RDS(on) [Static Drain-to-Source On-State Resistance], with test condition of VGS = 12V, ID = 45A			
For up to 500K Rads(Si), Low-Ohmic TO-254 only Change RDS(on) Max limit from 0.0066 Ω to 0.0076 Ω			
For 1000K Rads (Si), Low-Ohmic TO-254 only Change RDS(on) Max limit from 0.0070 Ω to 0.0080 Ω			
Reference: IR Datasheet PD-95838			
		16. APPROVING GOVERNMENT ACTIVITY	
17. GIDEP REPRESENTATIVE <b>Paul Hebert</b>		18. SIGNATURE 	19. DATE <b>November 5, 2015</b>